

PRELIMINARY

Notice : This is not a final specification
Some parametric are subject to change.

RT3JGGM

Composite Transistor
For high speed switching
Silicon P-channel MOSFET

DESCRIPTION

RT3JGGM is a composite transistor built with two INJ0103AX chips in SC-88 package.

FEATURE

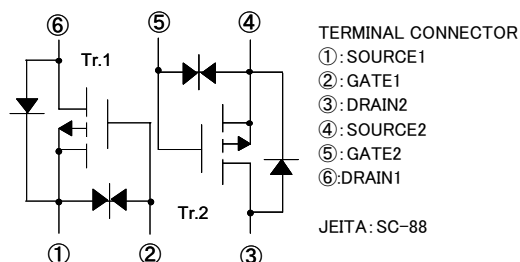
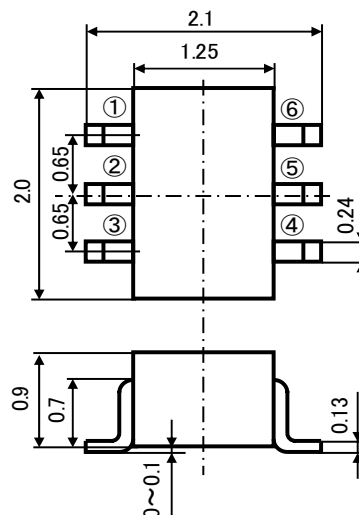
- Input impedance is high, and not necessary to consider a drive electric current.
- Drive voltage $-1.8V$
- Low on Resistance.
 $R_{DS(ON)}=0.67\Omega(TYP) @I_D=-400mA, V_{GS}=-4.5V$
 $R_{DS(ON)}=1.1\Omega(TYP) @I_D=-300mA, V_{GS}=-2.5V$
 $R_{DS(ON)}=1.6\Omega(TYP) @I_D=-10mA, V_{GS}=-1.8V$
- High speed switching.
- Small package for easy mounting.

APPLICATION

High speed switching , Analog switching

OUTLINE DRAWING

Unit:mm



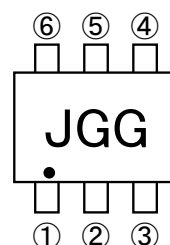
MAXIMUM RATING (Ta=25°C) (Tr1,Tr2 Common)

SYMBOL	PARAMETER	RATING	UNIT
VDSS	Drain-source voltage	-20	V
VGSS	Gate-source voltage	± 8	V
ID	Drain current(DC)	-550	mA
IDP	Drain current(Pulse)	$-2.2^{※1}$	A
PD	Total power dissipation	$600^{※2}$	mW
Tch	Channel temperature	+150	°C
Tstg	Range of Storage temperature	-55~+150	°C

※1: $P_w \leq 10\mu s$, Duty cycle $\leq 1\%$

※2: Package mounted on glass-epoxy substrate
(20mm×20mm×1mm , Cu pad 100mm²)

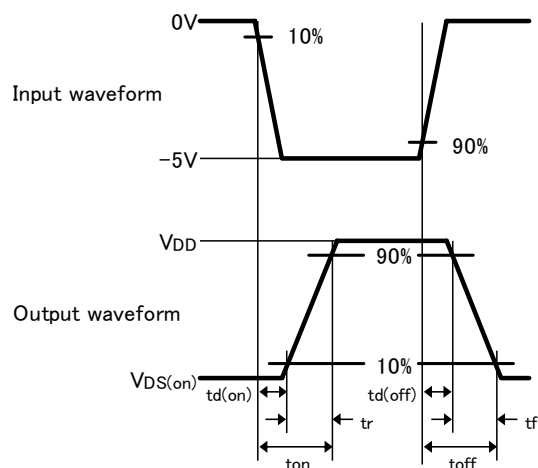
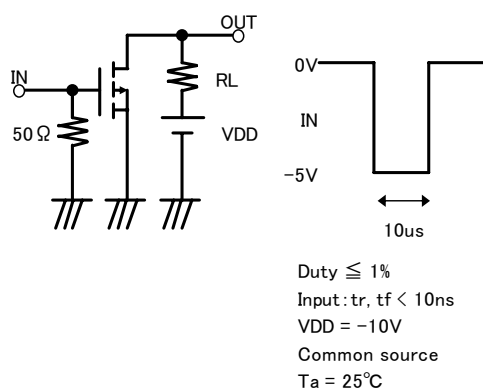
MARKING



ELECTRICAL CHARACTERISTICS (Ta=25°C) (Tr1,Tr2 Common)

SYMBOL	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V(BR)DSS	Drain-source breakdown voltage	ID=-100μA, VGS=0V	-20	-	-	V
IGSS	Gate-source leak current	VGS=±5V, VDS=0V	-	-	±0.5	μA
IDSS	Zero gate voltage drain current	VDS=-20V, VGS=0V	-	-	-1.0	μA
Vth	Gate threshold voltage	ID=-250μA, VDS=VGS	-0.6	-	-1.2	V
Yfs	Forward transfer admittance	VDS=-5V, ID=-200mA	-	400	-	mS
RDS(ON)	Static drain-source on-state resistance	ID=-400mA, VGS=-4.5V	-	0.67	-	Ω
		ID=-300mA, VGS=-2.5V	-	1.1	-	
		ID=-10mA, VGS=-1.8V	-	1.6	-	
Ciss	Input capacitance	VDS=-10V, VGS=0V, f=1MHz	-	60	-	pF
Coss	Output capacitance		-	16	-	pF
ton	Switching time	VDD=-5V, ID=-200mA VGS=0~-5V	-	50	-	ns
Toff			-	70	-	

Switching time test condition



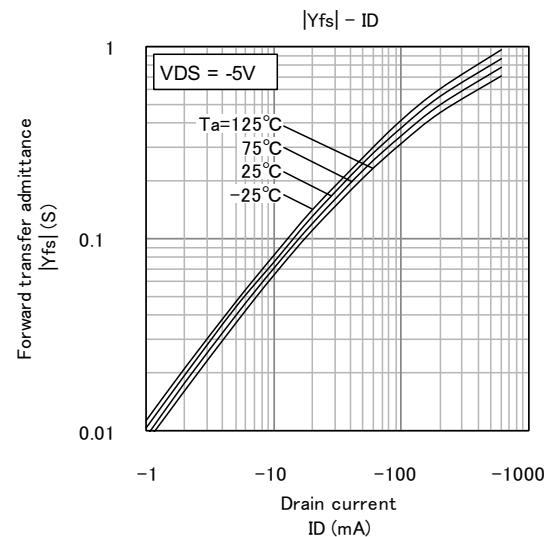
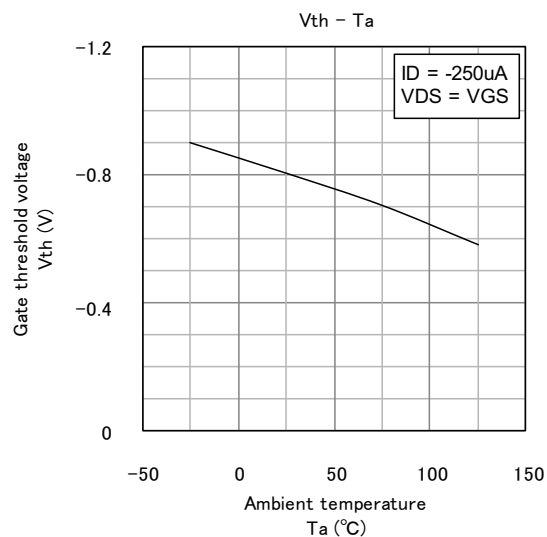
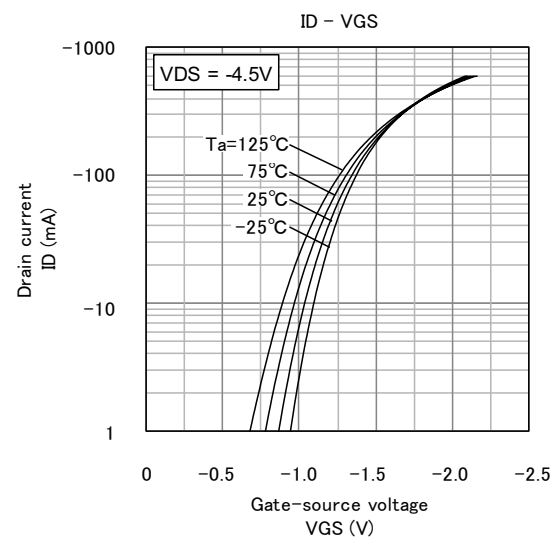
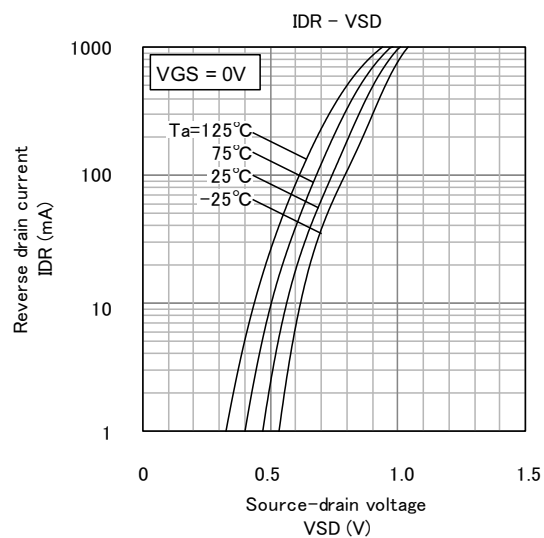
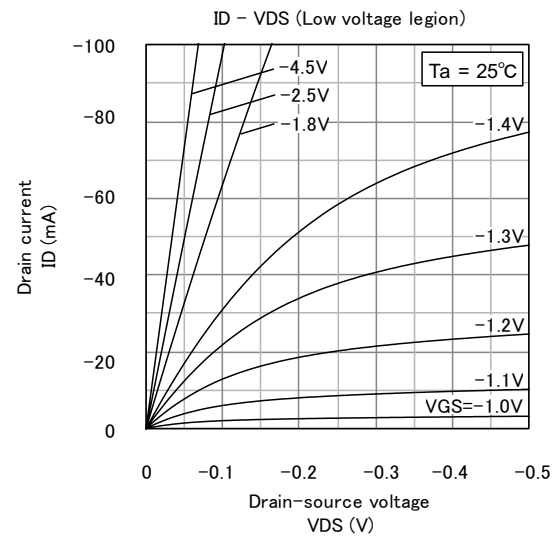
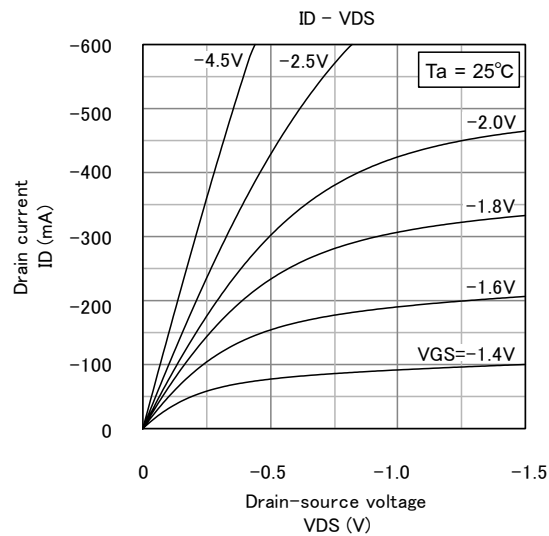
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TYPICAL CHARACTERISTICS

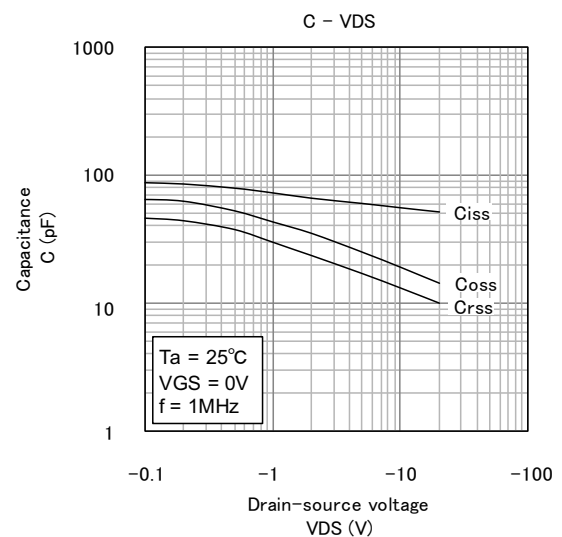
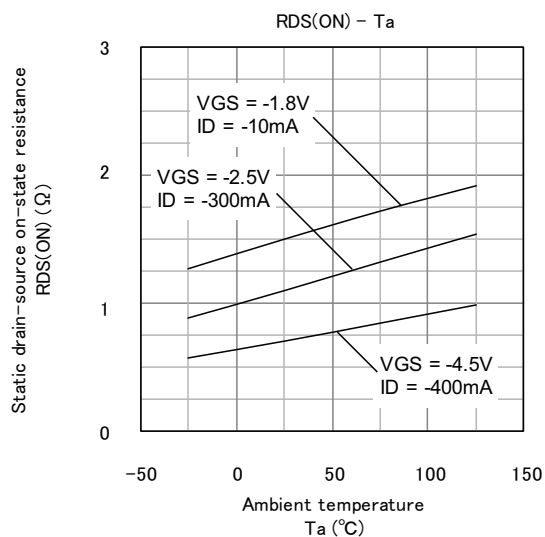
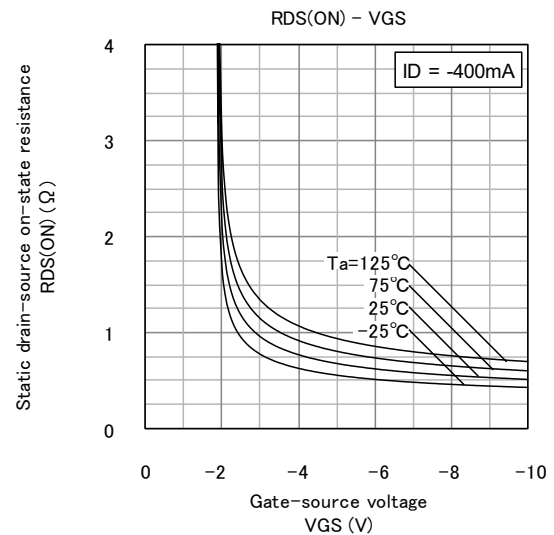
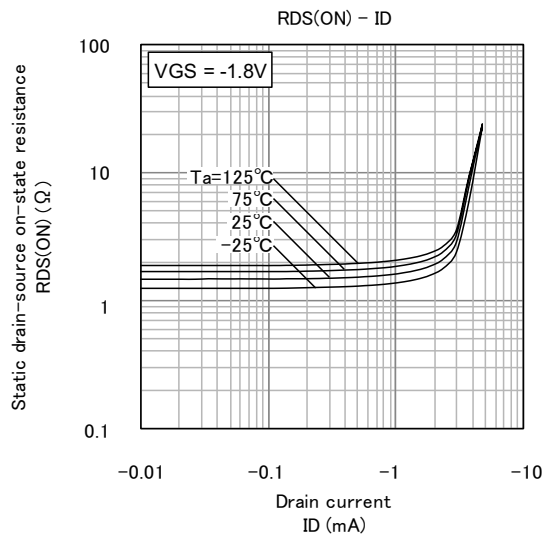
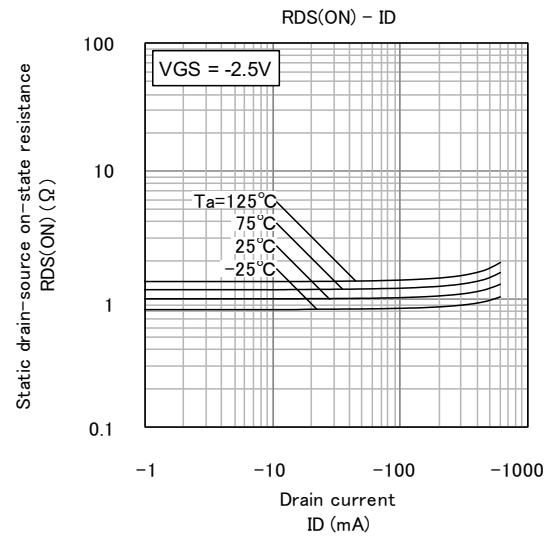
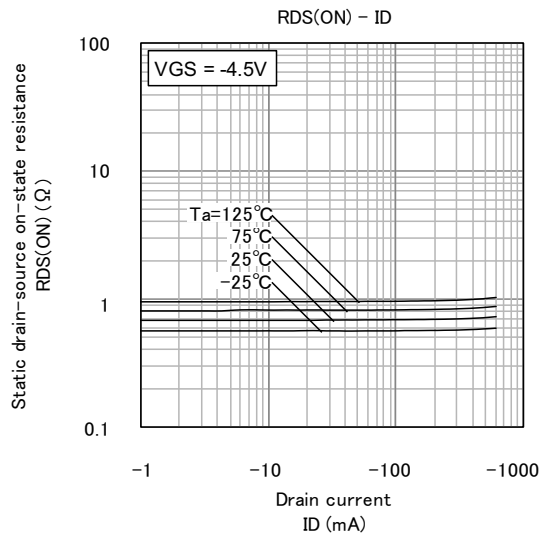


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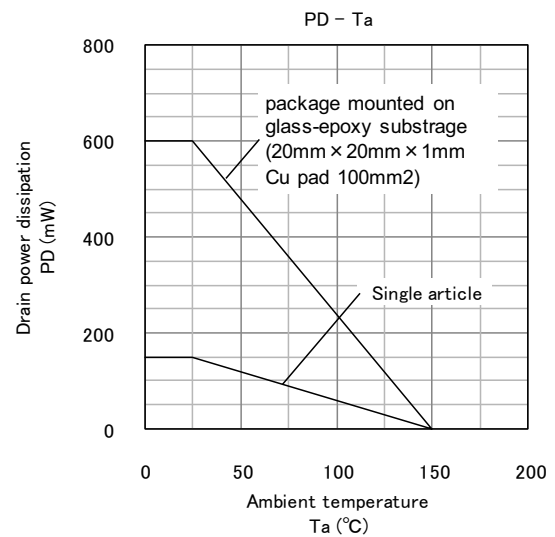
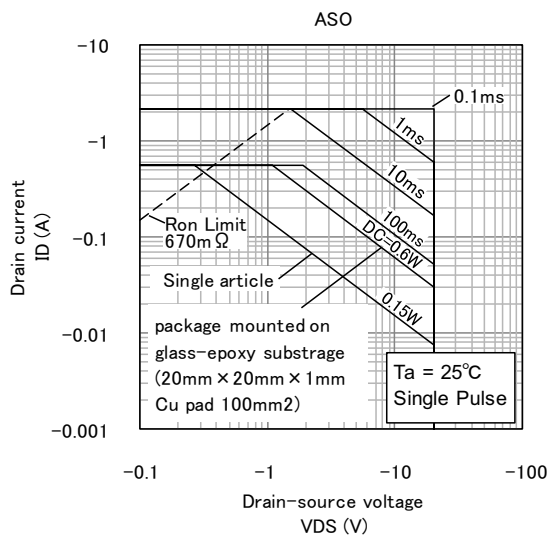
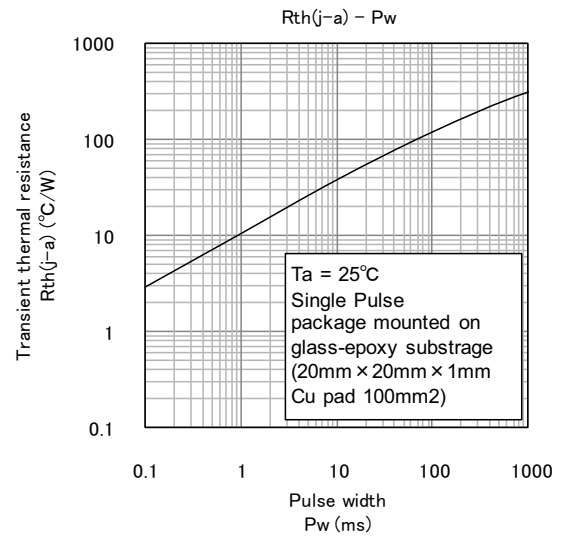
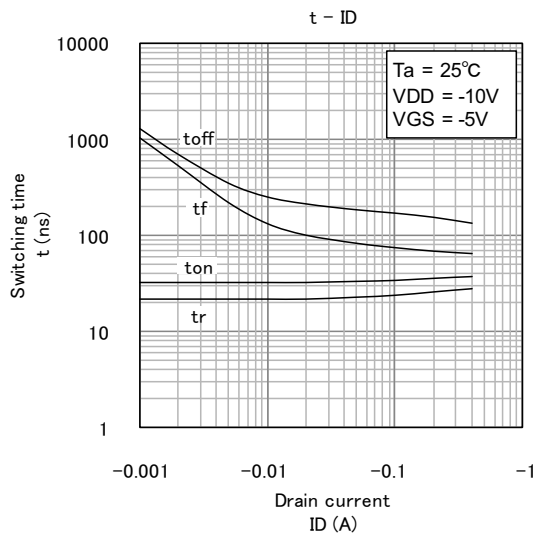


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